



AO4441

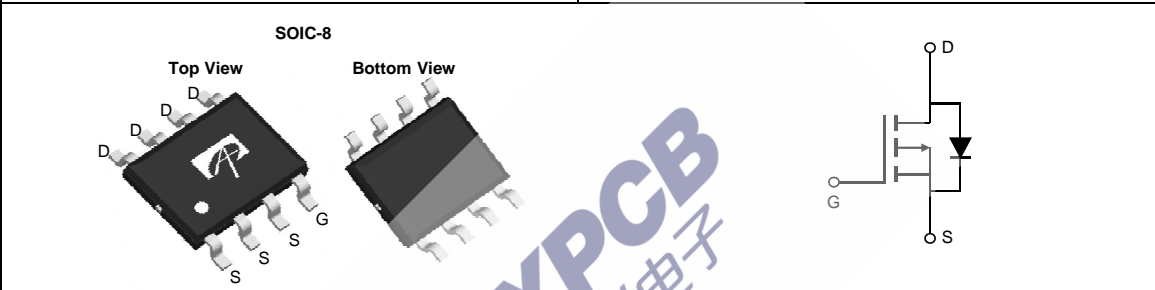
60V P-Channel MOSFET

General Description

The AO4441 uses advanced trench technology to provide excellent $R_{DS(ON)}$, and ultra-low low gate charge. This device is suitable for use as a load switch or in PWM applications.

Product Summary

V_{DS}	-60V
I_D (at $V_{GS}=-10V$)	-4A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	< 100m Ω
$R_{DS(ON)}$ (at $V_{GS} = -4.5V$)	< 130m Ω



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^A	I_D	$T_A=25^\circ C$	-4
		$T_A=70^\circ C$	-3.1
Pulsed Drain Current ^B	I_{DM}	-20	A
Power Dissipation ^A	P_D	$T_A=25^\circ C$	3.1
		$T_A=70^\circ C$	2
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A $t \leq 10s$	$R_{\theta JA}$	24	40	$^\circ C/W$
Maximum Junction-to-Ambient ^A Steady-State		54	75	$^\circ C/W$
Maximum Junction-to-Lead ^C Steady-State	$R_{\theta JL}$	21	30	$^\circ C/W$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-48V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1	-2.1	-3	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-4A T _J =125°C		80	100	mΩ
		V _{GS} =-4.5V, I _D =-3A		102	130	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-4A		10		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.77	-1	V
I _S	Maximum Body-Diode Continuous Current				-4	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance			930	1120	pF
C _{oss}	Output Capacitance	V _{GS} =0V, V _{DS} =-30V, f=1MHz		85		pF
C _{rss}	Reverse Transfer Capacitance			35		pF
R _g	Gate resistance	f=1MHz		7.2	9	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge			16	20	nC
Q _{g(4.5V)}	Total Gate Charge	V _{GS} =-10V, V _{DS} =-30V, I _D =-4A		8	10	nC
Q _{gs}	Gate Source Charge			2.5		nC
Q _{gd}	Gate Drain Charge			3.2		nC
t _{D(on)}	Turn-On DelayTime			8		ns
t _r	Turn-On Rise Time	V _{GS} =-10V, V _{DS} =-30V, R _L =7.5Ω,		3.8		ns
t _{D(off)}	Turn-Off DelayTime	R _{GEN} =3Ω		31.5		ns
t _f	Turn-Off Fall Time			7.5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-4A, di/dt=100A/μs		27	35	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-4A, di/dt=100A/μs		32		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The value in any a given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in ² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The SOA curve provides a single pulse rating.

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

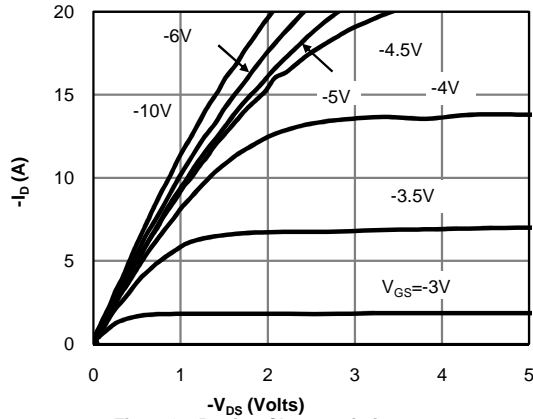


Fig 1: On-Region Characteristics

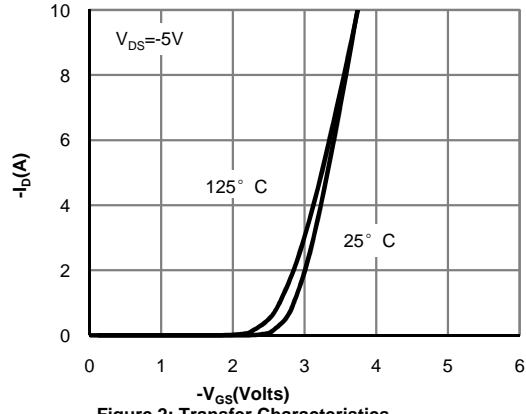


Figure 2: Transfer Characteristics

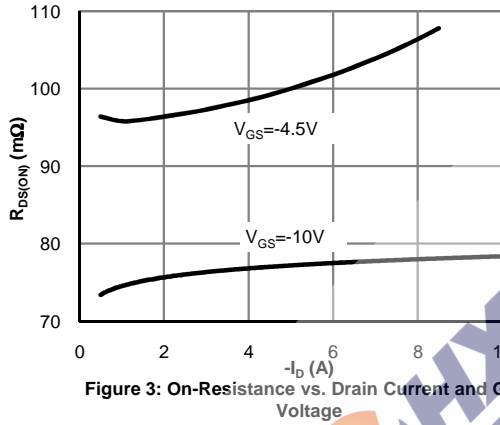


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

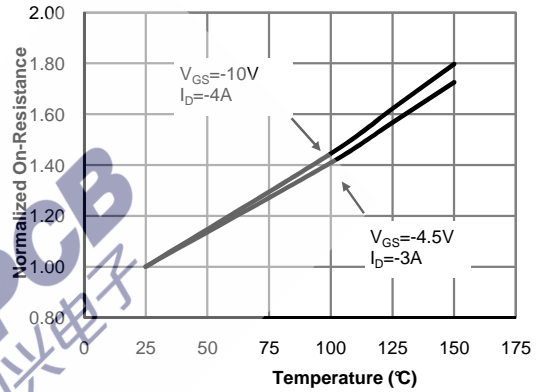


Figure 4: On-Resistance vs. Junction Temperature

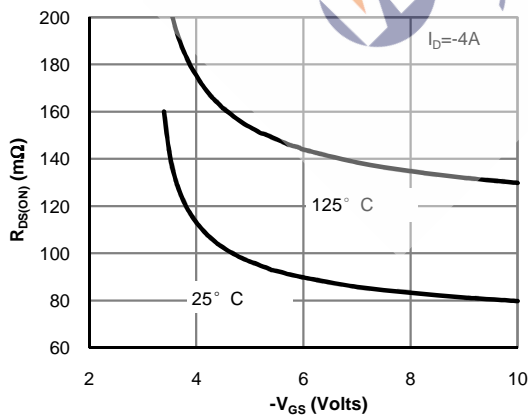


Figure 5: On-Resistance vs. Gate-Source Voltage

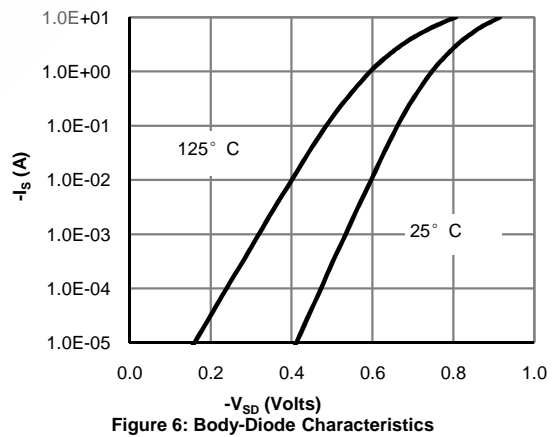


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

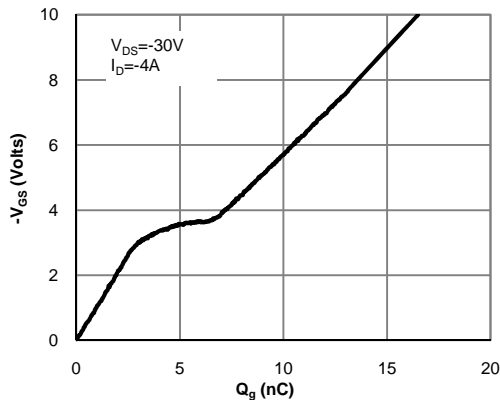


Figure 7: Gate-Charge Characteristics

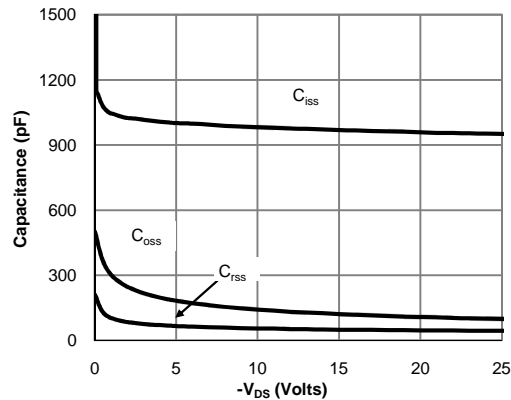


Figure 8: Capacitance Characteristics

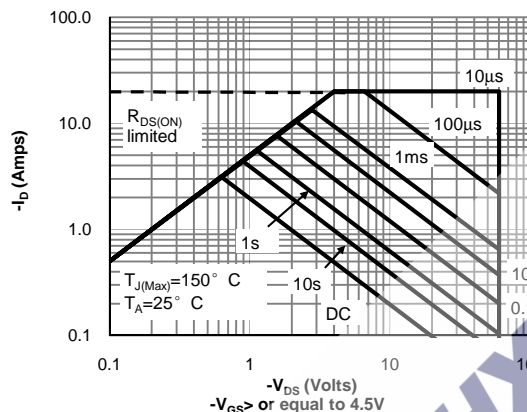


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

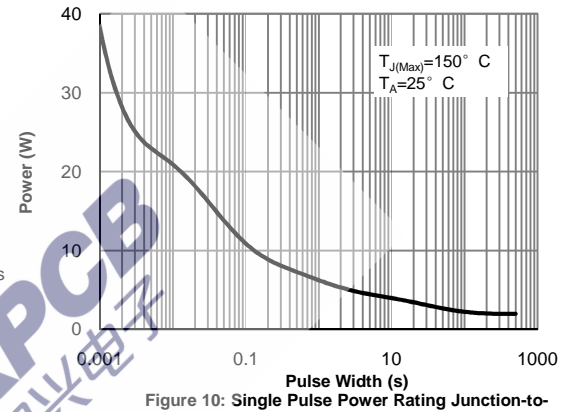


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

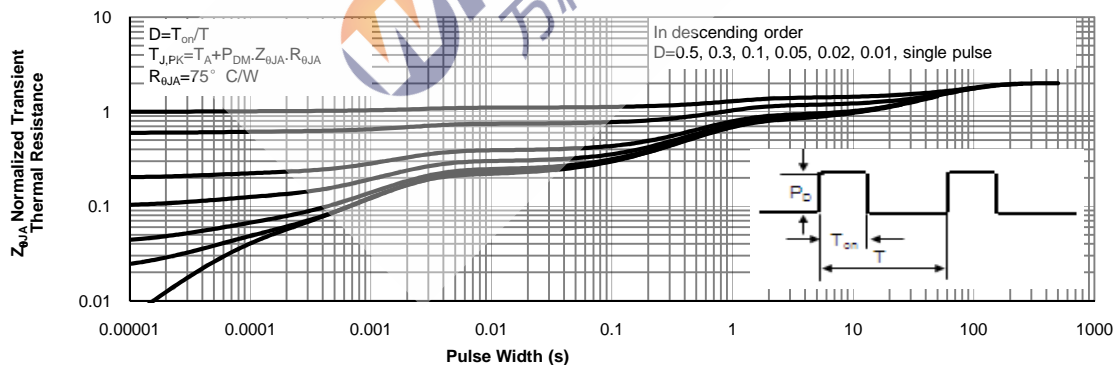
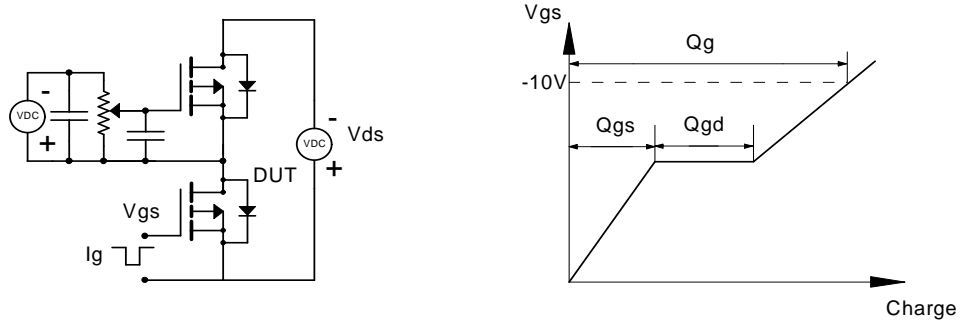
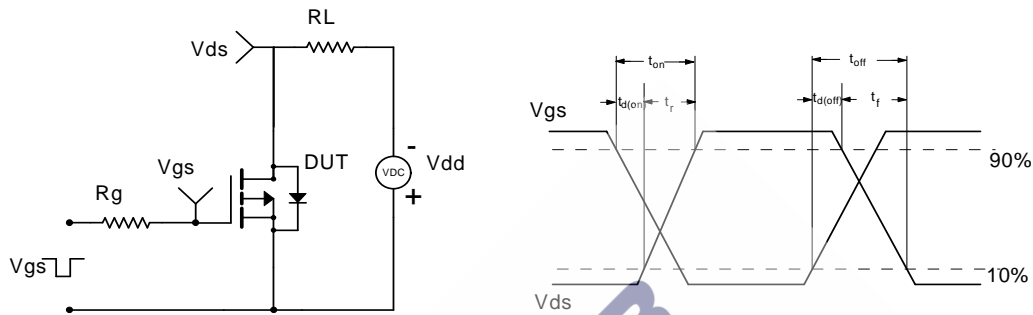


Figure 11: Normalized Maximum Transient Thermal Impedance

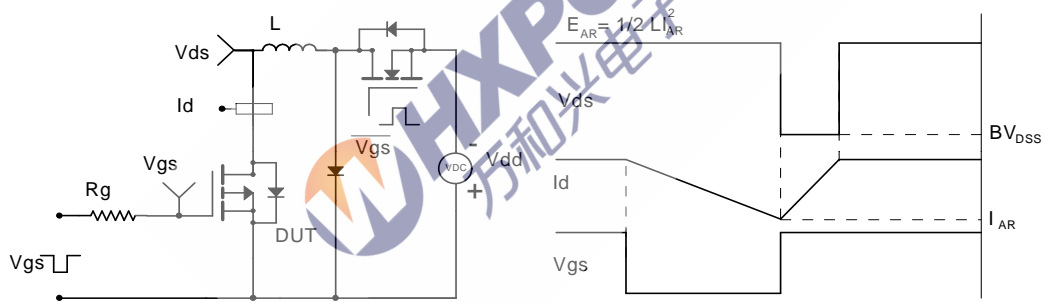
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

